MW39640AE

Diagonal 11 mm (type-2/3) IT CCD Area Image Sensor

■ Overview

The MW39640AE is a type-2/3 600k-pixel CCD solid state image sensor.

This device uses photodiodes in the opto-electric conversion section and CCDs for signal read-out. The electronic shutter function allows for an exposure time of 1/10000 seconds. Further, it features high sensitivity, low noise, broad dynamic range and low smear level.

The device has a total of 595728 pixels (1008 horizontal \times 591 vertical) and provides stable and clear images with a resolution of 700 horizontal and 420 vertical TV lines.

Part Number	CCD size	System	Color or B/W		
MW39640AE	11 mm (type-2/3)	CCIR	B/W		

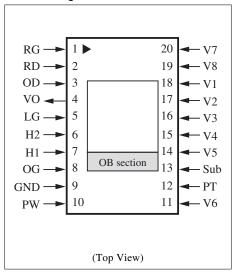
■ Features

- Effective pixel number: 954 (horizontal) × 585 (vertical)
- High sensitivity
- High resolution
- Low smear level
- Continuously variable-speed electronic shutter function

Applications

Three-chip CCD color video camera supporting a widescreen-TV

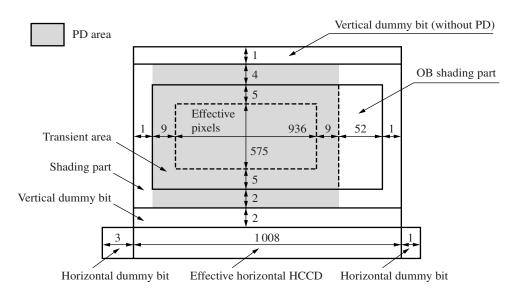
■ Pin Assignments



■ Device Configuration

Parameter	Value	Unit
Horizontal drive frequency	$f_{CK} = 1152f_{H} = 18.0$	MHz
Total pixel number	1008 (H) × 591 (V)	Pixel
Effective pixel number (including transient ones)	954 (H) × 585 (V)	Pixel
Effective pixel number	936 (H) × 575 (V)	Pixel
Pixel size	10.2 (H) × 9.4 (V)	μm²
Effective image sensor size	9.5472 (H) × 5.405 (V)	mm ²
Aspect ratio	16 : 9.058	H : V
Aspect ratio error	0.64	%

• Element Construction



■ Pin Descriptions

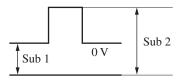
Pin No.	Symbol	Description	Pin No.	Symbol	Description
1	RG	Reset gate	11	V6	Vertical shift register clock pulse 6
2	RD	Reset drain	12	PT	P-well for protection circuit
3	OD	Output drain	13	Sub	Substrate
4	VO	Video output	14	V5	Vertical shift register clock pulse 5
5	LG	Output load transistor gate	15	V4	Vertical shift register clock pulse 4
6	H2	Horizontal shift register clock pulse 2	16	V3	Vertical shift register clock pulse 3
7	H1	Horizontal shift register clock pulse 1	17	V2	Vertical shift register clock pulse 2
8	OG	Output gate	18	V1	Vertical shift register clock pulse 1
9	GND	P-well	19	V8	Vertical shift register clock pulse 8
10	PW	P-well	20	V7	Vertical shift register clock pulse 7

■ Absolute Maximum Ratings and Operating Conditions

Parameter Lower limit Upper limit Min RG High 0 9 4.7 Low 0 — 6.7 RD 0 18 15.7 OD 0 18 15.7 VO — — — LG 0 5 2.7 Φ _{H2} High — 10 4.7 Low 0 — 0 Φ _{H1} High — 0 0 OG 0 5 0.3 GND Reference voltage — PW Reference voltage —	Typ Max 5.0 5.3 V 7.0 7.3 V 16.0 16.3 V 16.0 16.3 V
Low 0 — 6.7 RD 0 18 15.7 OD 0 18 15.7 VO — — — LG 0 5 2.7 ΦH2 High — 10 4.7 Low 0 — 0 ΦH1 High — 10 4.7 Low 0 — 0 OG 0 5 0.3 GND Reference voltage —	7.0 7.3 V 16.0 16.3 V 16.0 16.3 V — — V 3.0 3.3 V 5.0 5.3 V 0 0.3 V 5.0 5.3 V 0 0.3 V 0.5 1.0 V 0 — V
RD 0 18 15.7 OD 0 18 15.7 VO — — — LG 0 5 2.7 ΦH2 High — 10 4.7 Low 0 — 0 ΦH1 High — 10 4.7 Low 0 — 0 OG 0 5 0.3 GND Reference voltage —	16.0 16.3 V 16.0 16.3 V — — V 3.0 3.3 V 5.0 5.3 V 0 0.3 V 5.0 5.3 V 0 0.3 V 0 0.3 V 0.5 1.0 V 0 — V
OD 0 18 15.7 VO — — — LG 0 5 2.7 Φ _{H2} High — 10 4.7 Low 0 — 0 Φ _{H1} High — 10 4.7 Low 0 — 0 OG 0 5 0.3 GND Reference voltage —	16.0 16.3 V — — V 3.0 3.3 V 5.0 5.3 V 0 0.3 V 5.0 5.3 V 0 0.3 V 0.5 1.0 V 0 — V
VO — — — LG 0 5 2.7 Φ _{H2} High — 10 4.7 Low 0 — 0 Φ _{H1} High — 10 4.7 Low 0 — 0 OG 0 5 0.3 GND Reference voltage —	— — V 3.0 3.3 V 5.0 5.3 V 0 0.3 V 5.0 5.3 V 0 0.3 V 0.5 1.0 V 0 — V
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$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	5.0 5.3 V 0 0.3 V 5.0 5.3 V 0 0.3 V 0.5 1.0 V 0 — V
Low 0 — 0 \$\phi_{H1}\$ High — 10 4.7 Low 0 — 0 OG 0 5 0.3 GND Reference voltage —	0 0.3 V 5.0 5.3 V 0 0.3 V 0.5 1.0 V 0 V
φ _{H1} High — 10 4.7 Low 0 — 0 OG 0 5 0.3 GND Reference voltage —	5.0 5.3 V 0 0.3 V 0.5 1.0 V 0 — V
Low 0 — 0 OG 0 5 0.3 GND Reference voltage —	0 0.3 V 0.5 1.0 V 0 — V
OG 0 5 0.3 GND Reference voltage —	0.5 1.0 V 0 — V
GND Reference voltage —	0 — V
_	
PW Reference voltage —	0 77
1 Reference voltage	0 — V
ϕ_{V6} Middle — 5 -0.3	0 0.3 V
Low -12 — -9.3	-9.0 -8.7 V
PT -13.2 ϕ_{VL} $\phi_{VL} - 1$.	.2 $\phi_{VL} - 1.0$ $\phi_{VL} - 0.7$ V
Sub 1 * 0 18 5.0	adj. 14.5 V
Sub 2 * 0 45 24.5	25 + Sub 1 40.0 V
φ _{V5} High — 18 15.7	16.0 16.3 V
Middle — 5 -0.3	0 0.3 V
Low -12 — -9.3	-9.0 -8.7 V
φ _{V4} Middle — 5 –0.3	0 0.3 V
Low -12 — -9.3	-9.0 -8.7 V
ϕ_{V3} Middle — 5 -0.3	0 0.3 V
Low -12 -9.3	-9.0 -8.7 V
ϕ_{V2} Middle — 5 -0.3	0 0.3 V
Low -12 — -9.3	-9.0 -8.7 V
φ _{V1} High — 18 15.7	16.0 16.3 V
Middle — 5 -0.3	0 0.3 V
Low -12 — -9.3	-9.0 -8.7 V
ϕ_{V8} Middle — 5 -0.3	0 0.3 V
Low -12 — -9.3	-9.0 -8.7 V
ϕ_{V7} Middle — 5 -0.3	0 0.3 V
Low -12 — -9.3	-9.0 -8.7 V
Operating temperature -10 60 —	25 — °C
Storage temperature -30 70 —	°C

■ Absolute Maximum Ratings and Operating Conditions (continued)

Note) *: Sub pulse at the electronic shutter



■ Image Sensor Characteristics

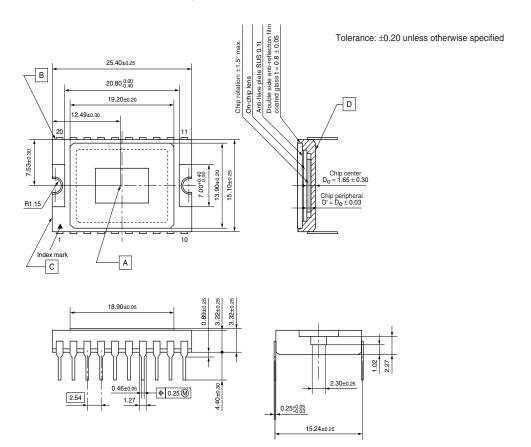
Parameter	Conditions	Min	Тур	Max	Unit	Remarks
S/N	25°C, Dark condition	63	64.5	_	dB	Standard output
Saturation output	25°C, F value adjust	1 500	_	_	mV	at CCD out
Standard output	25°C, J chart standard light intensity	560	620		mV	at CCD out
Image lag	25°C, 1/10 light intensity	_	0	_	%	Able to be swept out directly to substrate
Vertical smear	25°C, 1/10 V, F1.4	_	-130	-120	dB	Standard output
Transfer efficiency	25°C, F11 + 1/32ND	Resolution should not be reduced				
Electronic shutter	25°C, Specified driving	No abnormality within 1/100 to 1/2000 seconds				

Note) 1. The substrate voltage (Sub 1) should be adjusted to the minimum voltage that would not cause blooming, overflow and injection at image sensor of light input of 12800 times the standard light intensity.

^{2.} The standard light intensity is the one when the exposure is done at an aperture of F/11 using a light source of $2\,856K$ and 920 nt and placing a color temperature conversion filter LB-40 (HOYA) and an IR cutting filter CAW-500S (t = 2.5 mm) in the light path.

■ Package Dimensions (unit: mm)

• WDIP020-G-0600D (Lead-free package)



- 1. The package center does not meet the center of the effective pixel area. A is the center of the effective pixel area.
- The reference of a vertical direction(V) is the side B.
 The reference of a horizontal direction(H) is the side C.
 The reference of a height direction is the package bottom D.
- 3. The rotation precision of the effective pixel area: maximum $\pm 1.5^{\circ}$
- 4. The distance from the package bottom D to the effective pixel area : 1.65 mm \pm 0.3 mm
- 5. The tilt of the effective pixel area toward the package bottom D : Up to 60 μm (D' = $D_O \pm max.~0.03~mm)$
- 6. The thickness of the seal glass: 0.8 mm \pm 0.1 mm, and the refractive index: 1.50

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